

**In the Claims**

Claims 1-6 (cancelled).

Claim 7 (previously presented) A method of forming a transistor gate, comprising:  
forming one or more conductive materials over a semiconductor substrate;  
providing a photoresist block which is over a first portion of the one or more conductive materials and not over a second portion of the one or more conductive materials;

forming a layer over the photoresist block and over at least some of the second portion of the one or more conductive materials, the layer having a first segment that is against the photoresist block and a second segment that is not against the photoresist block;

treating the layer so that the first segment becomes different than the second segment;

after the treating, selectively removing the second segment of the layer while leaving the first segment of the layer; the photoresist block and remaining first segment together defining a masking block that is laterally wider than the photoresist block; and

transferring a pattern from the masking block to the one or more conductive materials to pattern a transistor gate construction from the one or more conductive materials.

Claim 8 (original): The method of claim 7 further comprising removing the masking block from over the transistor gate construction.

Claim 9 (original): The method of claim 7 further comprising defining a channel region within the semiconductor substrate beneath the transistor gate construction; and forming source/drain regions within the semiconductor substrate and spaced from one another by the channel region.

Claim 10 (previously presented): The method of claim 7 wherein the treatment includes causing the photoresist to release an acid which forms cross-links within the first segment of the layer.

Claims 11-23 (canceled).